





CND 101 - LAB [7]

MOSFET

(Metal-Oxide-Semiconductor Field -Effect Transistor)

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MOSFET CHARACTERISTICS

a. Graph 1 (I/Vds Characteristic for select regions of mosfet)

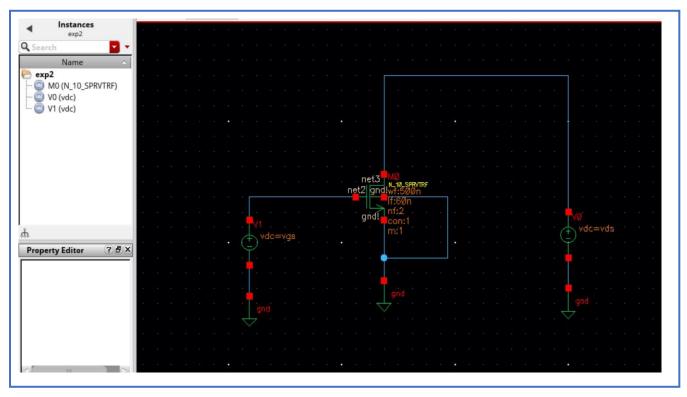


Figure 1 schematic of MOSFET with DC biasing voltage.

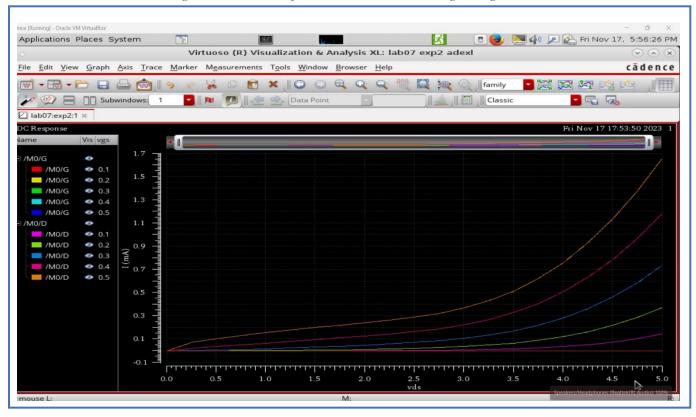


Figure 2 I/VDS characteristics.

b. Graph 2 (I/Vgs Characteristic for select regions of mosfet)

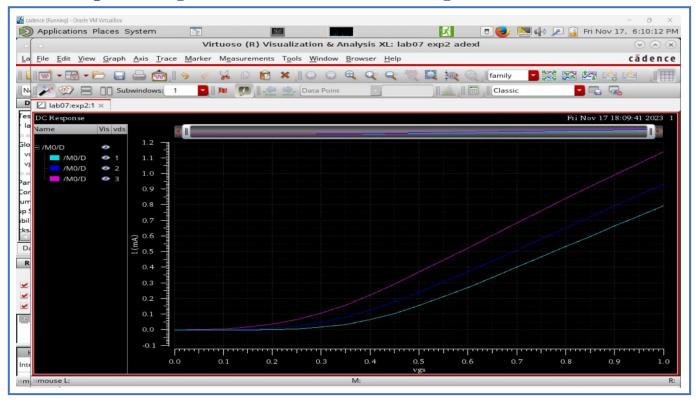


Figure 3 I/VGS characteristic.

Common source amplifier

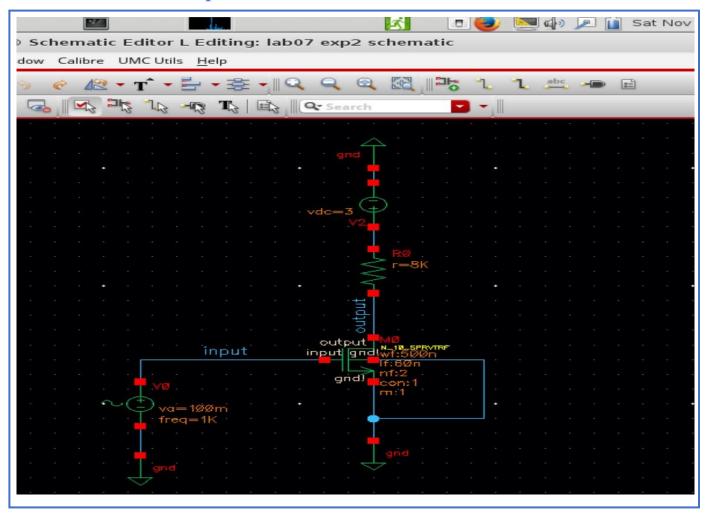


Figure 4 schematic of common source amplifier.

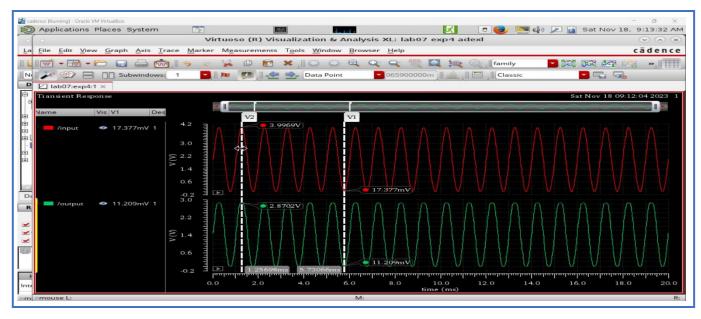
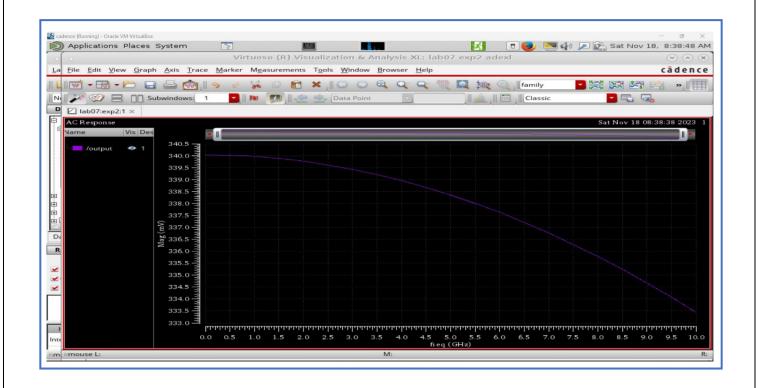


Figure 5 transient analysis of common source amplifier.



Common gate amplifier

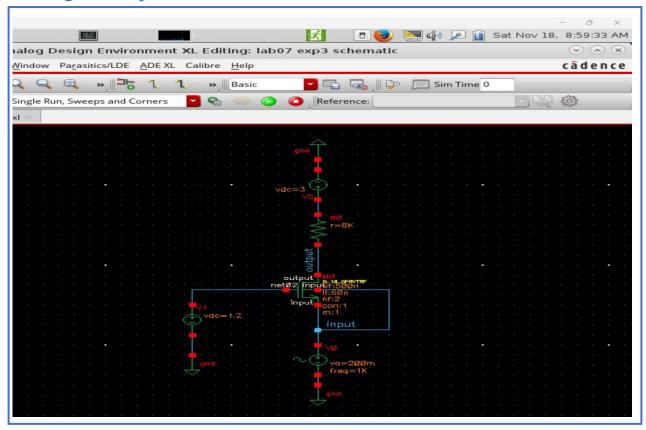


Figure 7 schematic of gate source amplifier.

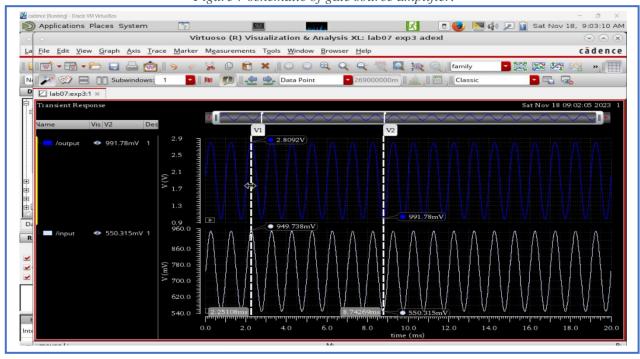
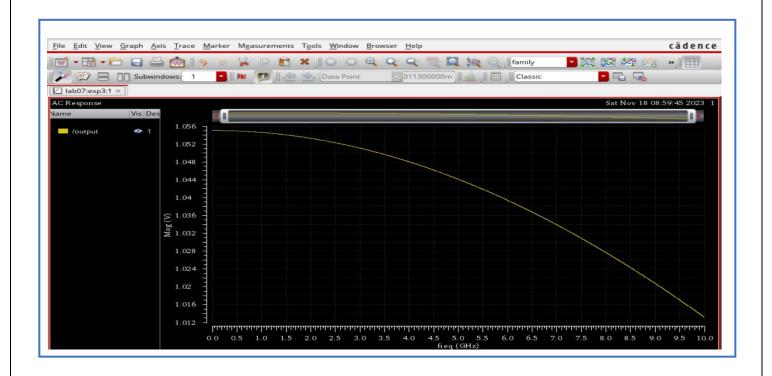


Figure 8 transient analysis of common gate amplifier.



common drain amplifier

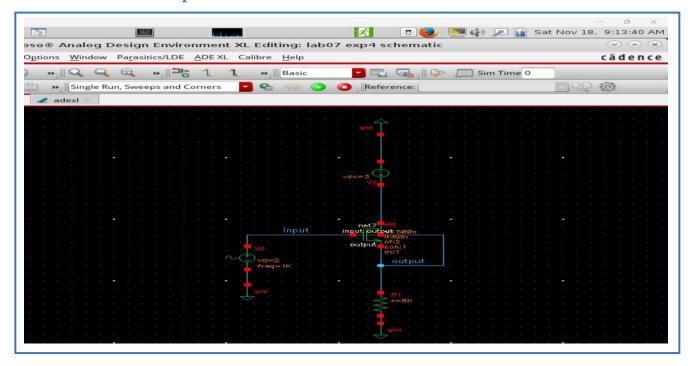


Figure 10 schematic of common drain amplifier.

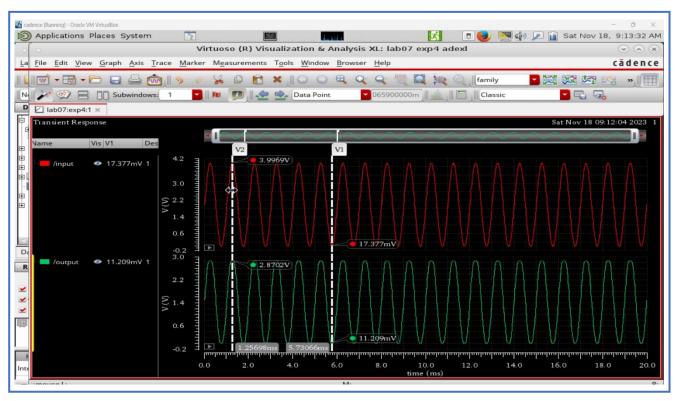
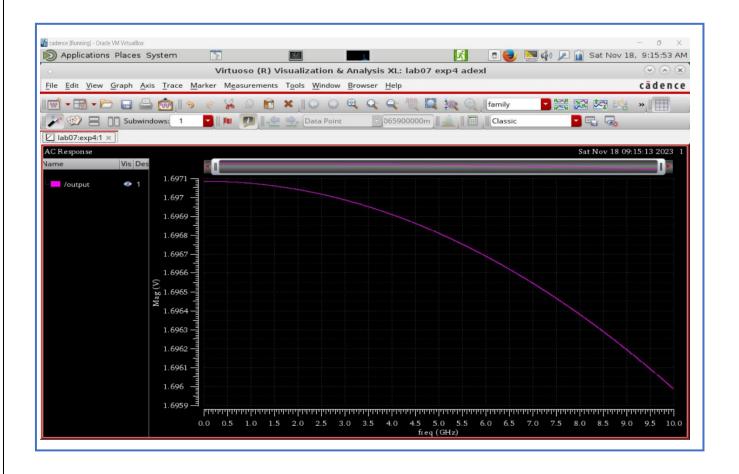


Figure 11 transient analysis of common drain amplifier.



Assignment 7

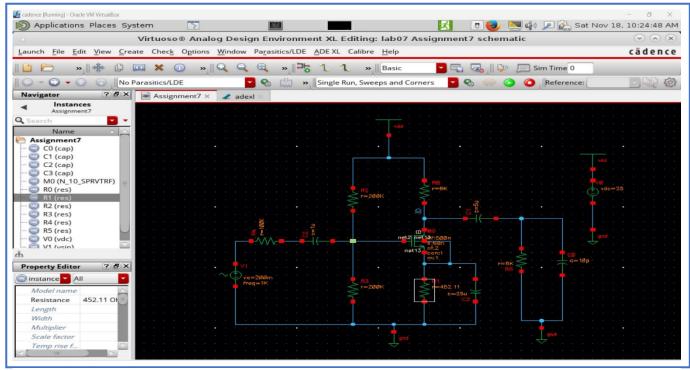


Figure 13 assignment 7 schematic (common source amplifier with capacitance to block DC signal).

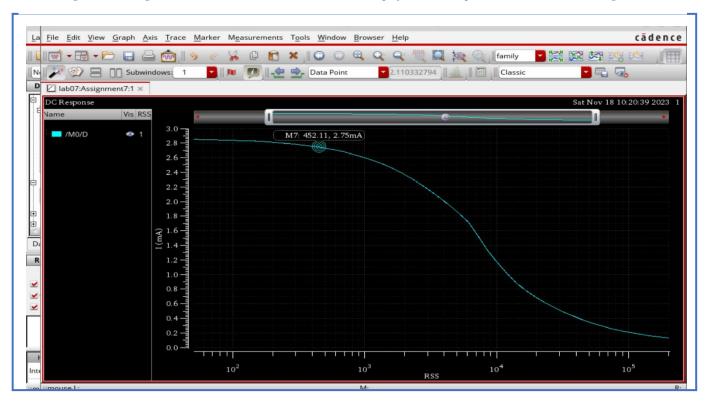
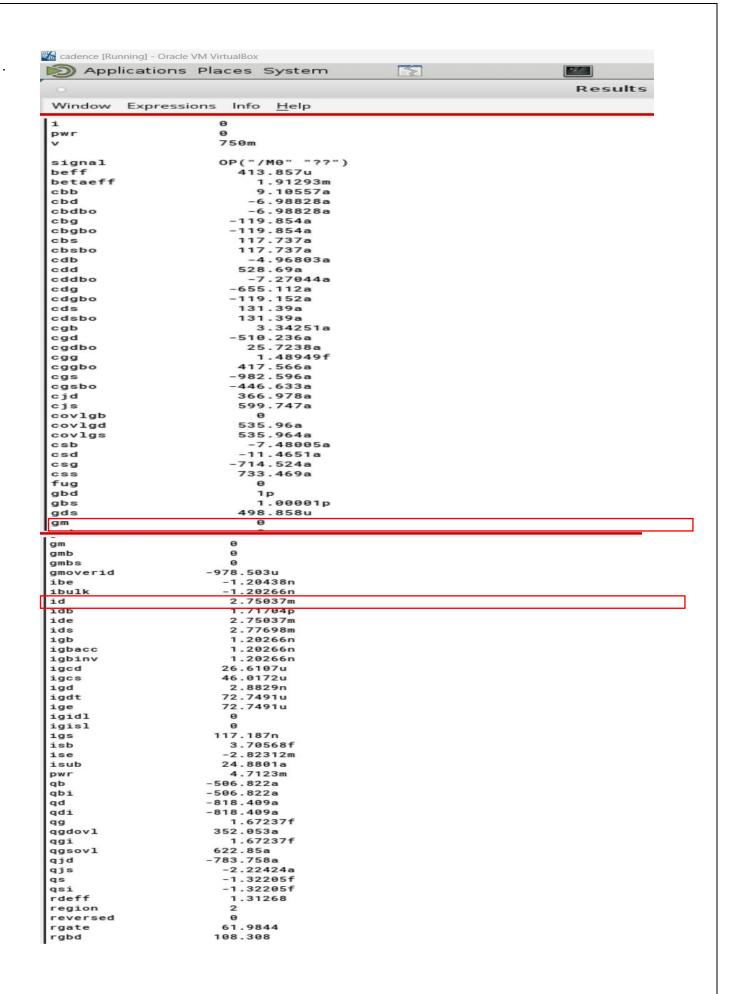
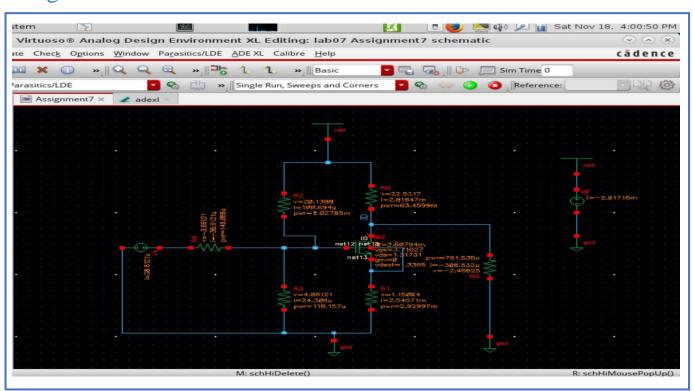


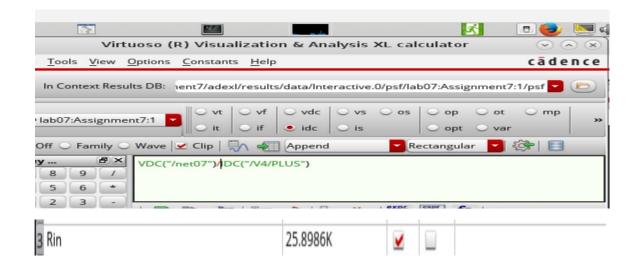
Figure 14 DC sweep analysis on RSS value



ron	619.61	
rout	2.00458K	
rseff	1.31268	
self_gain	0	
ueff	4.58045m	
vbs	0	
vdb	1.72065	
vds	1.72065	
vdsat	1.43331	
vdss	1.43331	
vearly	5.51334	
vgb	3.94892	
vgd	2.22828	
vgs	3.94892	
vgt	3.64574	
vsat_marg	287.337m	
vsb	- 0	
vth	303.186m	

To get Rin

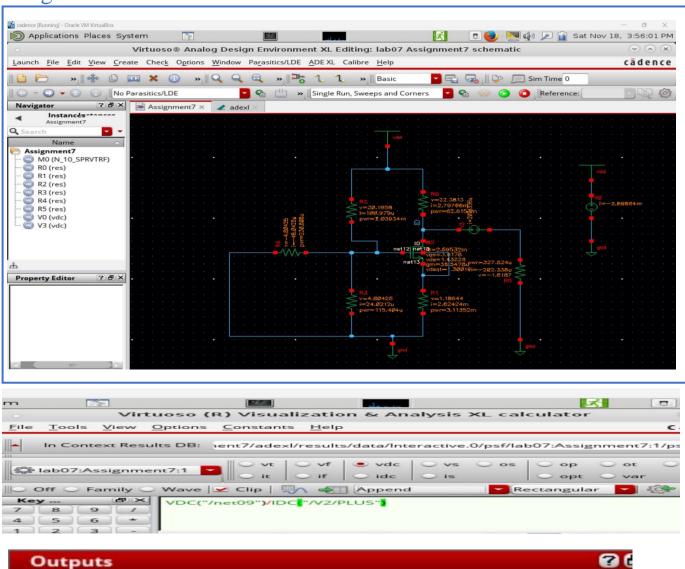




To get Rout

Name/Signal/Expr

1 Rout



Value 12.9422K